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PTOL-413A (09-04)
Approved for use through 07/31/2006. OMB 0651-0031
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Applicant Initiated Interview Request Form

Application No.: 10/840,125 First Named Applicant: Tino
Examiner: Crane, Sara W. Art Unit: 2811 Status of Application: Final Rejection

Tentative Participants:
(1) Mary Adams-Moe (2) _____
(3) _____ (4) _____

Proposed Date of Interview: 8/23/07 **Proposed Time:** 3:00 (AM/PM) Eastern

Type of Interview Requested:
(1) ☒ Telephonic (2) ☐ Personal (3) ☐ Video Conference

Exhibit To Be Shown or Demonstrated: ☐ YES ☐ NO
If yes, provide brief description: _____

Issues To Be Discussed

Issues (Rej., Obj., etc)	Claims/ Fig. #s	Prior Art	Discussed	Agreed	Not Agreed
(1) New matter objection			☐	☐	☐
(2) 112 rejection			☐	☐	☐
(3)			☐	☐	☐
(4)			☐	☐	☐

☐ Continuation Sheet Attached

Brief Description of Arguments to be Presented:

All matter was included in Specification as filed.

An interview was conducted on the above-identified application on _____.

NOTE: This form should be completed by applicant and submitted to the examiner in advance of the interview (see MPEP § 713.01).

This application will not be delayed from issue because of applicant's failure to submit a written record of this interview. Therefore, applicant is advised to file a statement of the substance of this interview (37 CFR 1.133(b)) as soon as possible.

Mary Adams-Moe
Applicant/Applicant's Representative Signature

Examiner/SPE Signature

Mary Adams-Moe
Typed/Printed Name of Applicant or Representative

57883
Registration Number, if applicable

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application: **Notched Spacer for CMOS transistors.**	§	
Application No.: **10/840,125**	§	Group Art Unit: **2811**
Filed: **05/06/2004**	§	Examiner: **Crane, Sara W**
Inventor: **Steve Ming Ting**	§	Attorney Docket No.: **TSM03-0945**

AGENDA FOR TELEPHONE INTERVIEW

Dear Examiner Crane,

I would like to schedule a phone interview with you concerning application number 10/840,125. I have recently been assigned this file. I would like to propose the following amendments as discussion points.

Paragraph 25

As illustrated in FIG. 1e, the portion of the first dielectric layer 126 (FIG. 1d) located under the notched-spacer masks 130 is removed due to the isotropic etch process, thereby creating a notched spacer. The width of the notch will be dependent upon the thickness of the first dielectric layer 126 and the notch height may be controlled by varying the etch duration. Furthermore, FIG. 1e illustrates the situation in which the first dielectric layer 126 is removed completely to the gate electrode 122. In other situations, the portion of the first dielectric layer 126, located under the notched-spacer masks 130 may remain on the side of the gate electrode 122, because of the inherent property of the isotropic etch to clear the thickest portion of dielectric layer 126 last. ~~This~~ Leaving a thin dielectric layer 126 on the lower portion of the side of the gate electrode 122 may be desirable, for example, when it is preferred to control the depth and angle of the implant or to protect the gate electrode 122 or gate dielectric 120 from damage during the etching process or other processes.

Claim 16

A method of forming a semiconductor device, the method comprising:

forming a gate electrode on a substrate, the substrate having a first conductivity type;

forming a notched spacer comprised of a single homogenous layer alongside the gate electrode, wherein a lower portion of the notched spacer is thinner than an upper portion of the notched spacer;

performing a first ion implant wherein only the gate electrode and the notched spacer act as masks during the first ion implant, the first ion implant using ions of the first conductivity type; and

performing one or more second ion implants using ions of a second conductivity type.

The afternoon of **Thursday 8/23 at 3:00 pm** Eastern time is the best time for me, however I will adjust my schedule to anytime that is convenient for you. Please confirm our appointment or suggest a new time.

Thank-you,
Best Regards,
Mary

Mary Adams-Moe
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